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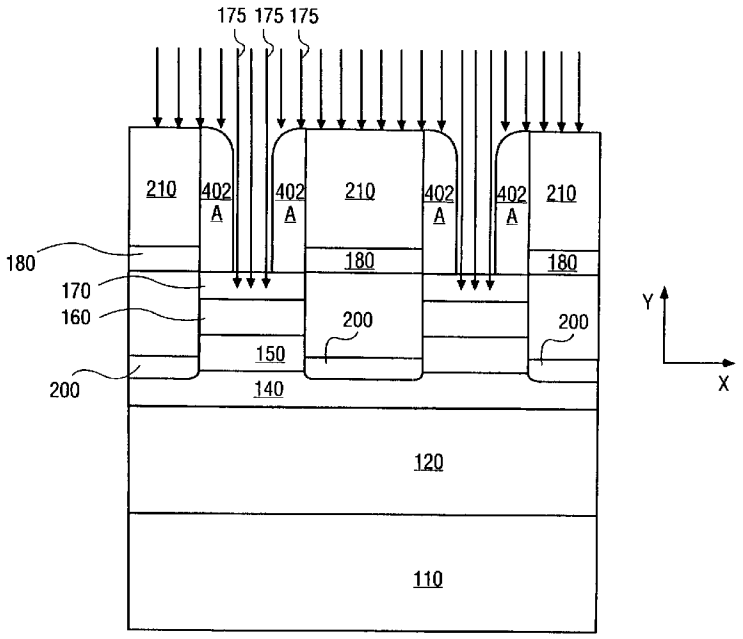
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(54) Title: MODIFIED CONTACT FOR PROGRAMMABLE DEVICES



(57) Abstract: In an aspect, an apparatus is provided that sets and reprograms the state of programmable devices. In an aspect, a method is provided such that an opening is formed through a dielectric (210) exposing a contact (170) formed on a substrate (110). The resistivity of the contact is modified by at least one of implanting ions (175) into the contact, depositing a material on the contact, and treating the contact with plasma. In an aspect, a spacer (102) is formed within the opening and programmable material (404), preferably a chalcopenide, is formed within the opening and on the modified contact. A conductor (410) is formed on the programmable material and the contact transmits to a signal line.

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